



MICRON.067DVL

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Ahmad ) Group Art Unit 2814  
Appl. No. : 09/397,952 )  
Filed : September 17, 1999 )  
For : FABRICATION OF )  
INTEGRATED DEVICES )  
USING NITROGEN )  
IMPLANTATION )  
Examiner : S. Rao )

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TECHNOLOGY CENTER 2800

AMENDMENT ACCOMPANYING RCE

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

Prior to examination on the merits following the Request for Continued Examination (RCE) filed herewith, please amend the application as indicated below.

In the Claims:

Please cancel Claim 2.

Please amend Claims 1, 3 and 23 as follows:

1. (Twice Amended) A process of forming a gate structure on a semiconductor substrate, comprising:

providing a semiconductor substrate having a channel region formed therein so as to define a source and a drain region and a gate structure comprised of a gate dielectric positioned on said channel region and a conductive layer positioned on said gate dielectric; implanting an insulator element region into said substrate; and transforming a portion of said conductive layer adjacent said insulator element region into a sidewall spacer after forming the insulator element region.

(Amended) The process of Claim 1, wherein said substrate comprises silicon.